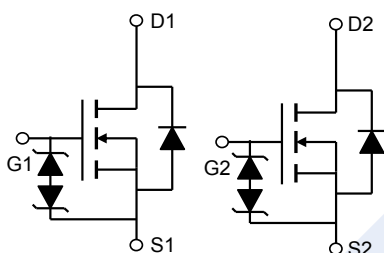
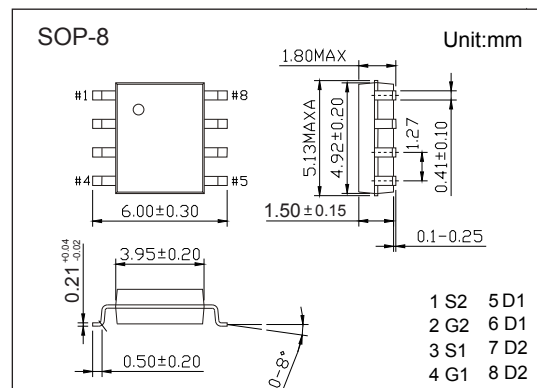


Dual N-Channel MOSFET

AO4854 (KO4854)

■ Features

- $V_{DS} (V) = 30V$
- $I_D = 8A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 19m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 23m\Omega$ ($V_{GS} = 4.5V$)
- $R_{DS(ON)} < 26m\Omega$ ($V_{GS} = 4V$)
- ESD Rating: 2KV HBM

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	8	A
	$T_A = 70^\circ C$		6.5	
Pulsed Drain Current		I_{DM}	48	
Avalanche Current		I_{AS}, I_{AR}	19	
Repetitive Avalanche Energy	$L = 0.1mH$	E_{AS}, E_{AR}	18	mJ
Power Dissipation	$T_A = 25^\circ C$	P_D	2	W
	$T_A = 70^\circ C$		1.3	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	62.5	$^\circ C/W$
	Steady-State		90	
Thermal Resistance.Junction- to-Lead		R_{thJL}	40	$^\circ C$
Junction Temperature		T_J	150	
Storage Temperature Range		T_{stg}	-55 to 150	

Dual N-Channel MOSFET

AO4854 (K04854)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
		V _{DS} =30V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±10	μA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2		2.4	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =8A			19	mΩ
		V _{GS} =10V, I _D =8A T _J =125°C			25	
		V _{GS} =4.5V, I _D =4A			23	
		V _{GS} =4V, I _D =4A			26	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	30			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =8A		30		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1MHz	600		888	pF
Output Capacitance	C _{oss}		77		145	
Reverse Transfer Capacitance	C _{rss}		50		115	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.5		1.7	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =15V, I _D =8A	12		18	nC
Total Gate Charge (4.5V)			6		9	
Gate Source Charge	Q _{gs}		2		3	
Gate Drain Charge	Q _{gd}		2		5	
Turn-On DelayTime	t _{d(on)}			5		ns
Turn-On Rise Time	t _r	V _{GS} =10V, V _{DS} =15V, R _L =1.8Ω, R _{GEN} =3Ω		3.5		
Turn-Off DelayTime	t _{d(off)}			19		
Turn-Off Fall Time	t _f			3.5		
Body Diode Reverse Recovery Time	t _{rr}		6		10	
Body Diode Reverse Recovery Charge	Q _{rr}	I _F = 8A, di/dt= 500A/us	14		22	nC
Maximum Body-Diode Continuous Current	I _S				2.5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note.The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4854 KA****
---------	----------------

Dual N-Channel MOSFET

AO4854 (KO4854)

■ Typical Characteristics

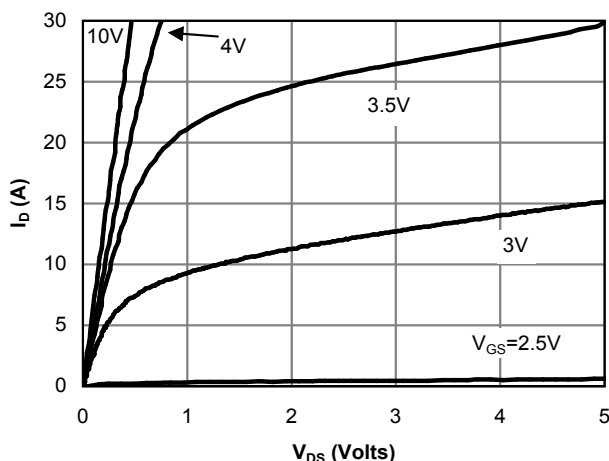


Fig 1: On-Region Characteristics (Note E)

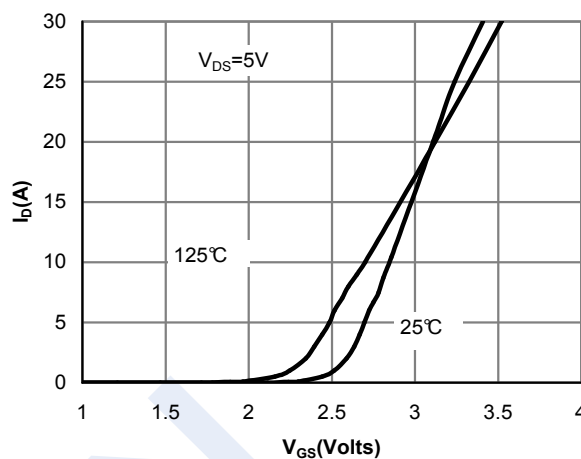


Figure 2: Transfer Characteristics (Note E)

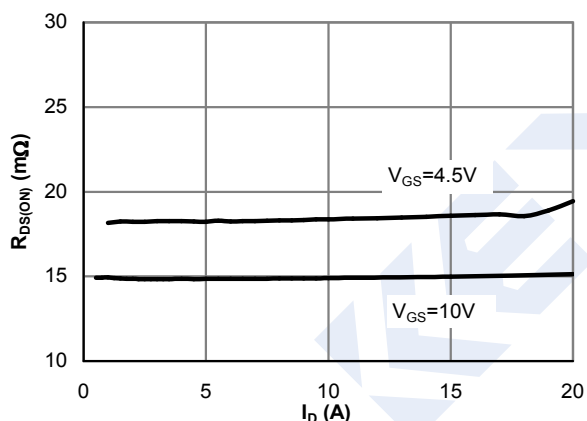


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

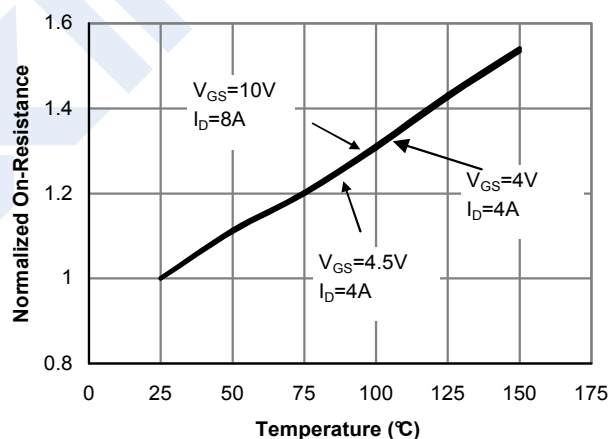


Figure 4: On-Resistance vs. Junction Temperature (Note E)

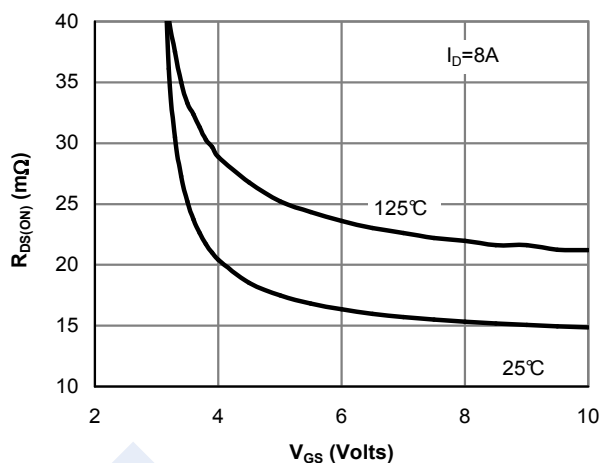


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

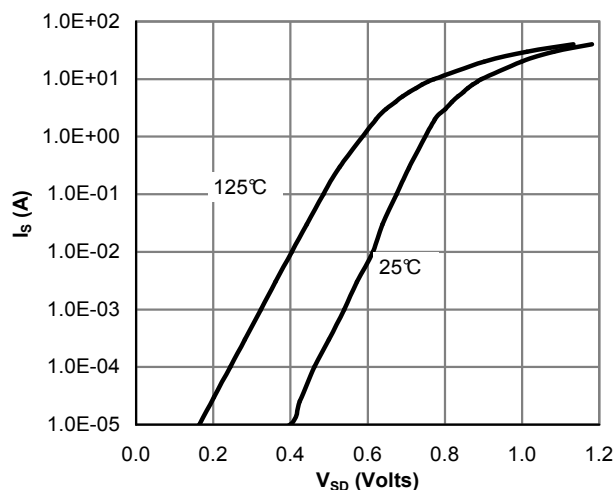


Figure 6: Body-Diode Characteristics (Note E)

Dual N-Channel MOSFET

AO4854 (KO4854)

■ Typical Characteristics

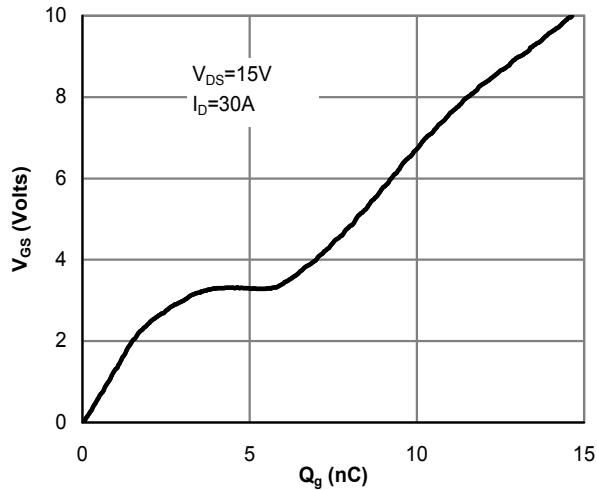


Figure 7: Gate-Charge Characteristics

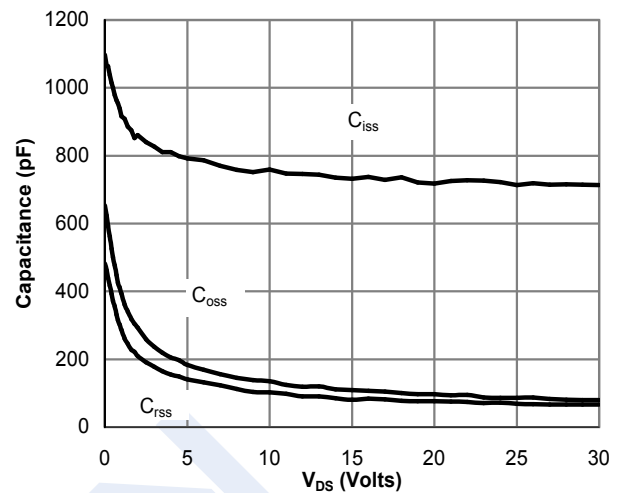


Figure 8: Capacitance Characteristics

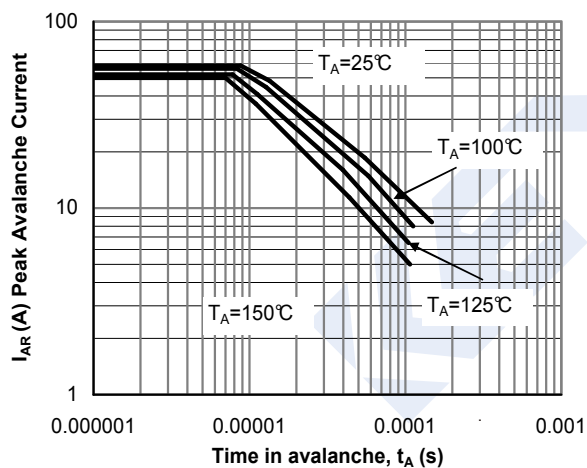


Figure 9: Single Pulse Avalanche capability (Note C)

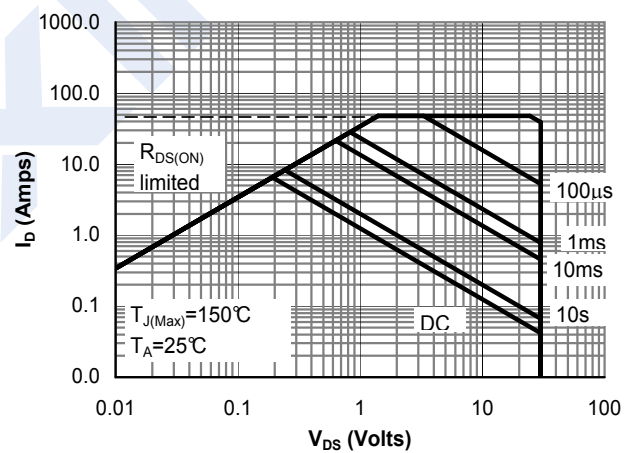


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

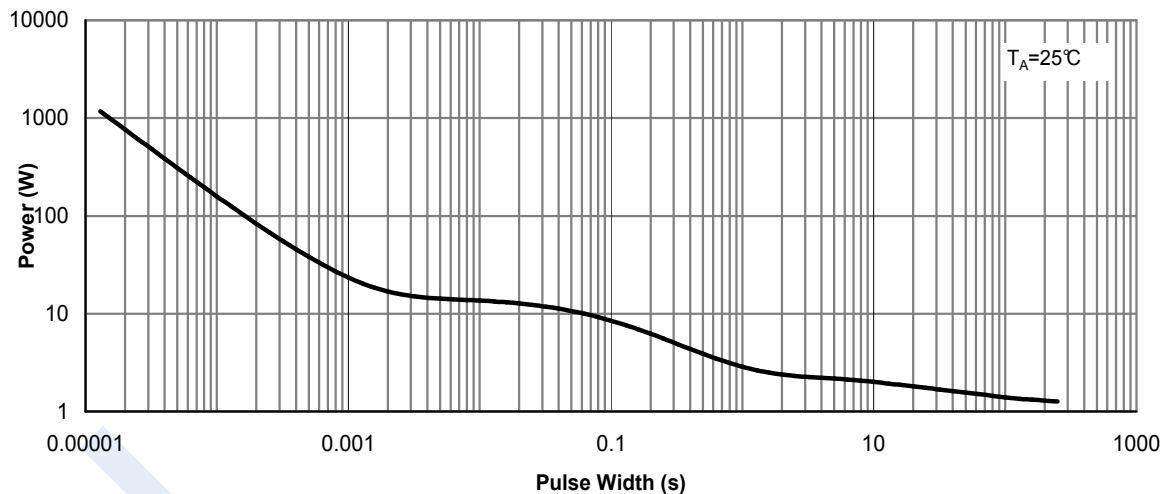


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

Dual N-Channel MOSFET

AO4854 (KO4854)

■ Typical Characteristics

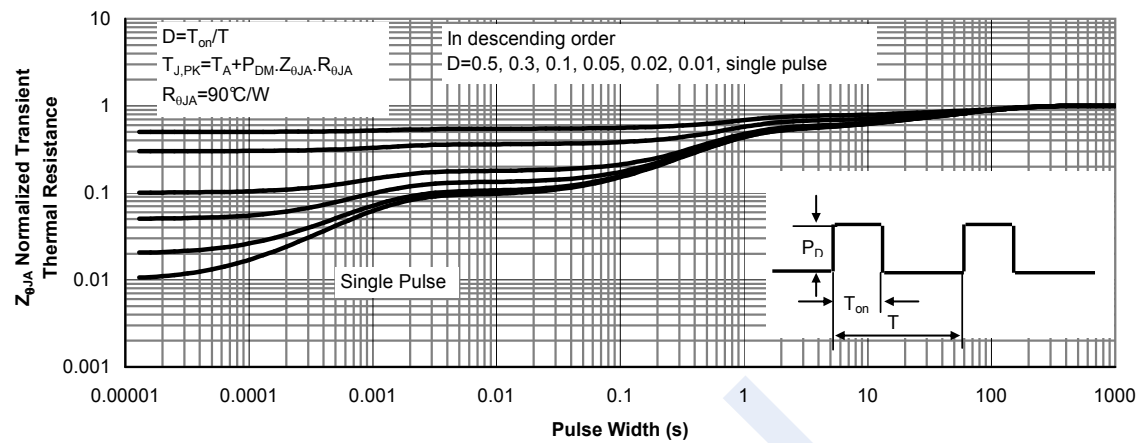


Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)